

08/ 866,129

UNITED STATES PATENT AND TRADEMARK OFFICE  
**CERTIFICATE OF CORRECTION**

PATENT NO. : 6,734,468 B2  
DATED : May 11, 2004  
INVENTOR(S) : Toshiya Uemura et al.

Page 1 of 1

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

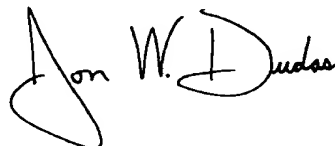
Column 10,

Line 64, should read:

4. The light-emitting semiconductor device according to claim 1, wherein said electrode layer has a multi-layer structure having at least a first electrode layer formed on said surface layer and a second electrode layer formed on said first electrode layer, wherein said first electrode layer comprises material having an ionization potential that is lower than that of said second electrode layer, said material of said second electrode layer, has an ohmic characteristic to said surface layer better than that of said first electrode layer, and said material of said second electrode layer being distributed more deeply into said surface layer than that of said first electrode layer by heat treatment.

Signed and Sealed this

Seventeenth Day of May, 2005

A handwritten signature in black ink, appearing to read "Jon W. Dudas". The signature is stylized with a large, looped initial "J" and a distinct "D" at the end.

JON W. DUDAS  
*Director of the United States Patent and Trademark Office*